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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	276480
Number of I/O	147
Number of Gates	1500000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m1a3pe1500-pq208

1 – ProASIC3E Device Family Overview

General Description

ProASIC3E, the third-generation family of Microsemi flash FPGAs, offers performance, density, and features beyond those of the ProASIC PLUS® family. Nonvolatile flash technology gives ProASIC3E devices the advantage of being a secure, low power, single-chip solution that is Instant On. ProASIC3E is reprogrammable and offers time-to-market benefits at an ASIC-level unit cost. These features enable designers to create high-density systems using existing ASIC or FPGA design flows and tools.

ProASIC3E devices offer 1 kbit of on-chip, programmable, nonvolatile FlashROM storage as well as clock conditioning circuitry based on six integrated phase-locked loops (PLLs). ProASIC3E devices have up to three million system gates, supported with up to 504 kbits of true dual-port SRAM and up to 620 user I/Os.

Several ProASIC3E devices support the Cortex-M1 soft IP cores, and the ARM-Enabled devices have Microsemi ordering numbers that begin with M1A3PE.

Flash Advantages

Reduced Cost of Ownership

Advantages to the designer extend beyond low unit cost, performance, and ease of use. Unlike SRAM-based FPGAs, flash-based ProASIC3E devices allow all functionality to be Instant On; no external boot PROM is required. On-board security mechanisms prevent access to all the programming information and enable secure remote updates of the FPGA logic. Designers can perform secure remote in-system reprogramming to support future design iterations and field upgrades with confidence that valuable intellectual property (IP) cannot be compromised or copied. Secure ISP can be performed using the industry-standard AES algorithm. The ProASIC3E family device architecture mitigates the need for ASIC migration at higher user volumes. This makes the ProASIC3E family a cost-effective ASIC replacement solution, especially for applications in the consumer, networking/ communications, computing, and avionics markets.

Security

The nonvolatile, flash-based ProASIC3E devices do not require a boot PROM, so there is no vulnerable external bitstream that can be easily copied. ProASIC3E devices incorporate FlashLock, which provides a unique combination of reprogrammability and design security without external overhead, advantages that only an FPGA with nonvolatile flash programming can offer.

ProASIC3E devices utilize a 128-bit flash-based lock and a separate AES key to provide the highest level of protection in the FPGA industry for programmed intellectual property and configuration data. In addition, all FlashROM data in ProASIC3E devices can be encrypted prior to loading, using the industry-leading AES-128 (FIPS192) bit block cipher encryption standard. The AES standard was adopted by the National Institute of Standards and Technology (NIST) in 2000 and replaces the 1977 DES standard. ProASIC3E devices have a built-in AES decryption engine and a flash-based AES key that make them the most comprehensive programmable logic device security solution available today. ProASIC3E devices with AES-based security provide a high level of protection for secure, remote field updates over public networks such as the Internet, and ensure that valuable IP remains out of the hands of system overbuilders, system cloners, and IP thieves.

Security, built into the FPGA fabric, is an inherent component of the ProASIC3E family. The flash cells are located beneath seven metal layers, and many device design and layout techniques have been used to make invasive attacks extremely difficult. The ProASIC3E family, with FlashLock and AES security, is unique in being highly resistant to both invasive and noninvasive attacks. Your valuable IP is protected with industry-standard security, making remote ISP possible. A ProASIC3E device provides the best available security for programmable logic designs.

Advanced Architecture

The proprietary ProASIC3E architecture provides granularity comparable to standard-cell ASICs. The ProASIC3E device consists of five distinct and programmable architectural features (Figure 1-1 on page 3):

- FPGA VersaTiles
- Dedicated FlashROM
- Dedicated SRAM/FIFO memory
- Extensive CCCs and PLLs
- Pro I/O structure

The FPGA core consists of a sea of VersaTiles. Each VersaTile can be configured as a three-input logic function, a D-flip-flop (with or without enable), or a latch by programming the appropriate flash switch interconnections. The versatility of the ProASIC3E core tile as either a three-input lookup table (LUT) equivalent or as a D-flip-flop/latch with enable allows for efficient use of the FPGA fabric. The VersaTile capability is unique to the ProASIC family of third-generation architecture Flash FPGAs. VersaTiles are connected with any of the four levels of routing hierarchy. Flash switches are distributed throughout the device to provide nonvolatile, reconfigurable interconnect programming. Maximum core utilization is possible for virtually any design.

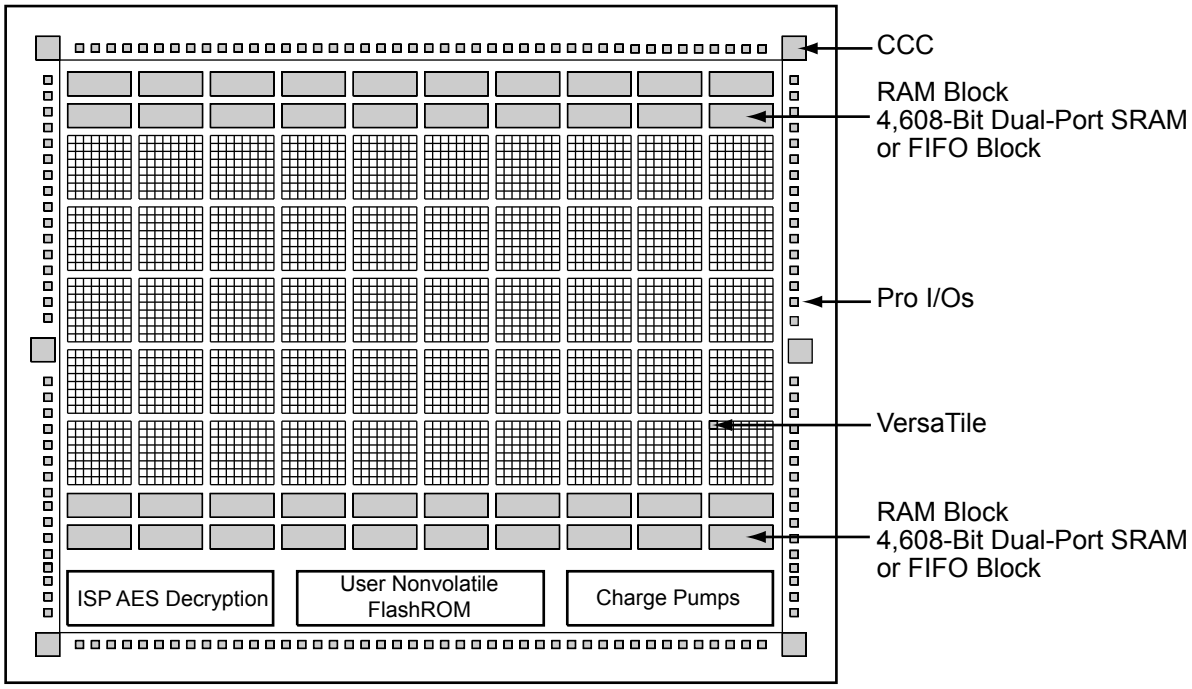

Figure 1-1 • **ProASIC3E Device Architecture Overview**

Power Calculation Methodology

This section describes a simplified method to estimate power consumption of an application. For more accurate and detailed power estimations, use the SmartPower tool in the Libero SoC software.

The power calculation methodology described below uses the following variables:

- The number of PLLs as well as the number and the frequency of each output clock generated
- The number of combinatorial and sequential cells used in the design
- The internal clock frequencies
- The number and the standard of I/O pins used in the design
- The number of RAM blocks used in the design
- Toggle rates of I/O pins as well as VersaTiles—guidelines are provided in Table 2-11 on page 2-11.
- Enable rates of output buffers—guidelines are provided for typical applications in Table 2-12 on page 2-11.
- Read rate and write rate to the memory—guidelines are provided for typical applications in Table 2-12 on page 2-11. The calculation should be repeated for each clock domain defined in the design.

Methodology

Total Power Consumption—P_{TOTAL}

$P_{TOTAL} = P_{STAT} + P_{DYN}$

P_{STAT} is the total static power consumption.

P_{DYN} is the total dynamic power consumption.

Total Static Power Consumption—P_{STAT}

$P_{STAT} = PDC1 + N_{INPUTS} * PDC2 + N_{OUTPUTS} * PDC3$

N_{INPUTS} is the number of I/O input buffers used in the design.

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

Total Dynamic Power Consumption—P_{DYN}

$P_{DYN} = P_{CLOCK} + P_{S\text{-}CELL} + P_{C\text{-}CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL}$

Global Clock Contribution—P_{CLOCK}

$P_{CLOCK} = (PAC1 + N_{SPINE} * PAC2 + N_{ROW} * PAC3 + N_{S\text{-}CELL} * PAC4) * F_{CLK}$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3E FPGA Fabric User's Guide*.

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3E FPGA Fabric User's Guide*.

F_{CLK} is the global clock signal frequency.

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design.

PAC1, PAC2, PAC3, and PAC4 are device-dependent.

Sequential Cells Contribution—$P_{S\text{-}CELL}$

$P_{S\text{-}CELL} = N_{S\text{-}CELL} * (PAC5 + \alpha_1 / 2 * PAC6) * F_{CLK}$

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-11 on page 2-11.

F_{CLK} is the global clock signal frequency.

Detailed I/O DC Characteristics

***Table 2-18* • Input Capacitance**

Symbol	Definition	Conditions	Min.	Max.	Units
C_{IN}	Input capacitance	VIN = 0, f = 1.0 MHz		8	pF
C_{INCLK}	Input capacitance on the clock pin	VIN = 0, f = 1.0 MHz		8	pF

***Table 2-19* • I/O Output Buffer Maximum Resistances[1]**

Standard	Drive Strength	$R_{PULL\text{-}DOWN}$ (Ω)[2]	$R_{PULL\text{-}UP}$ (Ω)[3]
3.3 V LVTTL / 3.3 V LVCMOS	4 mA	100	300
	8 mA	50	150
	12 mA	25	75
	16 mA	17	50
	24 mA	11	33
3.3 V LVCMOS Wide Range	100 µA	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	4 mA	100	200
	8 mA	50	100
	12 mA	25	50
	16 mA	20	40
	24 mA	11	22
1.8 V LVCMOS	2 mA	200	225
	4 mA	100	112
	6 mA	50	56
	8 mA	50	56
	12 mA	20	22
	16 mA	20	22
1.5 V LVCMOS	2 mA	200	224
	4 mA	100	112
	6 mA	67	75
	8 mA	33	37
	12 mA	33	37
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	25	75
3.3 V GTL	20 mA[4]	11	–
2.5 V GTL	20 mA[4]	14	–

Notes:

1. *These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on VCCI, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located on the Microsemi SoC Products Group website at www.microsemi.com/index.php?option=com_content&id=1671&lang=en&view=article.*
2. *$R_{(PULL\text{-}DOWN\text{-}MAX)}$ = (VOLspec) / IOLspec*
3. *$R_{(PULL\text{-}UP\text{-}MAX)}$ = (VCCImax – VOHspec) / IOHspec*
4. *Output drive strength is below JEDEC specification.*

2.5 V LVCMOS

Low-Voltage CMOS for 2.5 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 2.5 V applications.

Table 2-33 • Minimum and Maximum DC Input and Output Levels

2.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[1]	IIH[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max., V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	µA[4]	µA[4]
4 mA	–0.3	0.7	1.7	3.6	0.7	1.7	4	4	18	16	10	10
8 mA	–0.3	0.7	1.7	3.6	0.7	1.7	8	8	37	32	10	10
12 mA	–0.3	0.7	1.7	3.6	0.7	1.7	12	12	74	65	10	10
16 mA	–0.3	0.7	1.7	3.6	0.7	1.7	16	16	87	83	10	10
24 mA	–0.3	0.7	1.7	3.6	0.7	1.7	24	24	124	169	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*
3. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

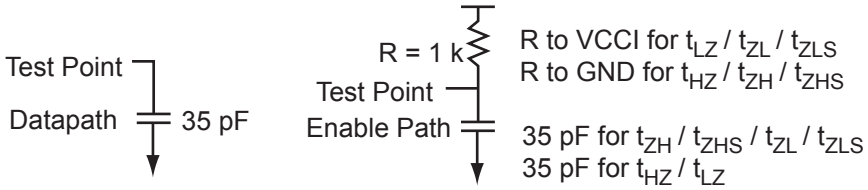

Figure 2-8 • AC Loading

Table 2-34 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	C_{LOAD} (pF)
0	2.5	1.2	–	35

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

Timing Characteristics

Table 2-35 • 2.5 V LVCMOS High Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.66	8.82	0.04	1.51	1.66	0.43	8.13	8.82	2.72	2.29	10.37	11.05	ns
	–1	0.56	7.50	0.04	1.29	1.41	0.36	6.92	7.50	2.31	1.95	8.82	9.40	ns
	–2	0.49	6.58	0.03	1.13	1.24	0.32	6.07	6.58	2.03	1.71	7.74	8.25	ns
8 mA	Std.	0.66	5.27	0.04	1.51	1.66	0.43	5.27	5.27	3.10	3.03	7.50	7.51	ns
	–1	0.56	4.48	0.04	1.29	1.41	0.36	4.48	4.48	2.64	2.58	6.38	6.38	ns
	–2	0.49	3.94	0.03	1.13	1.24	0.32	3.93	3.94	2.32	2.26	5.60	5.61	ns
12 mA	Std.	0.66	3.74	0.04	1.51	1.66	0.43	3.81	3.49	3.37	3.49	6.05	5.73	ns
	–1	0.56	3.18	0.04	1.29	1.41	0.36	3.24	2.97	2.86	2.97	5.15	4.87	ns
	–2	0.49	2.80	0.03	1.13	1.24	0.32	2.85	2.61	2.51	2.61	4.52	4.28	ns
16 mA	Std.	0.66	3.53	0.04	1.51	1.66	0.43	3.59	3.12	3.42	3.62	5.83	5.35	ns
	–1	0.56	3.00	0.04	1.29	1.41	0.36	3.06	2.65	2.91	3.08	4.96	4.55	ns
	–2	0.49	2.63	0.03	1.13	1.24	0.32	2.68	2.33	2.56	2.71	4.35	4.00	ns
24 mA	Std.	0.66	3.26	0.04	1.51	1.66	0.43	3.32	2.48	3.49	4.11	5.56	4.72	ns
	–1	0.56	2.77	0.04	1.29	1.41	0.36	2.83	2.11	2.97	3.49	4.73	4.01	ns
	–2	0.49	2.44	0.03	1.13	1.24	0.32	2.48	1.85	2.61	3.07	4.15	3.52	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.*

3.3 V PCI, 3.3 V PCI-X

Peripheral Component Interface for 3.3 V standard specifies support for 33 MHz and 66 MHz PCI Bus applications.

Table 2-45 • Minimum and Maximum DC Input and Output Levels

3.3 V PCI/PCI-X	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[1]	IIH[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	µA[4]	µA[4]
Per PCI specification	Per PCI curves										10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V< VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN< VCCI. Input current is larger when operating outside recommended ranges.*
3. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*

AC loadings are defined per the PCI/PCI-X specifications for the datapath; Microsemi loadings for enable path characterization are described in Figure 2-11.

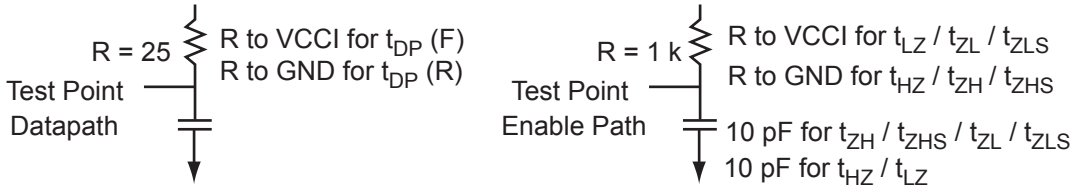

Figure 2-11 • AC Loading

AC loadings are defined per PCI/PCI-X specifications for the datapath; Microsemi loading for tristate is described in Table 2-46.

Table 2-46 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	C_{LOAD} (pF)
0	3.3	0.285 * VCCI for $t_{DP(R)}$ 0.615 * VCCI for $t_{DP(F)}$	–	10

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

Timing Characteristics

Table 2-47 • 3.3 V PCI/PCI-X
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.66	2.81	0.04	1.05	1.67	0.43	2.86	2.00	3.28	3.61	5.09	4.23	ns
–1	0.56	2.39	0.04	0.89	1.42	0.36	2.43	1.70	2.79	3.07	4.33	3.60	ns
–2	0.49	2.09	0.03	0.78	1.25	0.32	2.13	1.49	2.45	2.70	3.80	3.16	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

Table 2-78 • LVDS Minimum and Maximum DC Input and Output Levels

DC Parameter	Description	Min.	Typ.	Max.	Units
VCCI	Supply Voltage	2.375	2.5	2.625	V
VOL	Output Low Voltage	0.9	1.075	1.25	V
VOH	Output High Voltage	1.25	1.425	1.6	V
IOL[1]	Output Lower Current	0.65	0.91	1.16	mA
IOH[1]	Output High Current	0.65	0.91	1.16	mA
VI	Input Voltage	0		2.925	V
IIH[2]	Input High Leakage Current			10	µA
IIL[2]	Input Low Leakage Current			10	µA
VODIFF	Differential Output Voltage	250	350	450	mV
VOCM	Output Common Mode Voltage	1.125	1.25	1.375	V
VICM	Input Common Mode Voltage	0.05	1.25	2.35	V
VIDIFF	Input Differential Voltage [2]	100	350		mV

Notes:

1. *IOL/IOH defined by VODIFF/(Resistor Network).*
2. *Currents are measured at 85°C junction temperature.*

Table 2-79 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)
1.075	1.325	Cross point	–

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

***Table 2-84* • Parameter Definition and Measuring Nodes**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	H, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	F, H
t_{OHD}	Data Hold Time for the Output Data Register	F, H
t_{OSUE}	Enable Setup Time for the Output Data Register	G, H
t_{OHE}	Enable Hold Time for the Output Data Register	G, H
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	L, DOUT
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	L, H
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	L, H
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	H, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	J, H
t_{OEHD}	Data Hold Time for the Output Enable Register	J, H
t_{OESUE}	Enable Setup Time for the Output Enable Register	K, H
t_{OEHE}	Enable Hold Time for the Output Enable Register	K, H
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	I, EOUT
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	I, H
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	I, H
t_{ICLKQ}	Clock-to-Q of the Input Data Register	A, E
t_{ISUD}	Data Setup Time for the Input Data Register	C, A
t_{IHD}	Data Hold Time for the Input Data Register	C, A
t_{ISUE}	Enable Setup Time for the Input Data Register	B, A
t_{IHE}	Enable Hold Time for the Input Data Register	B, A
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	D, E
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	D, A
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	D, A

*Note: *See Figure 2-25 on page 2-53 for more information.*

Output Register

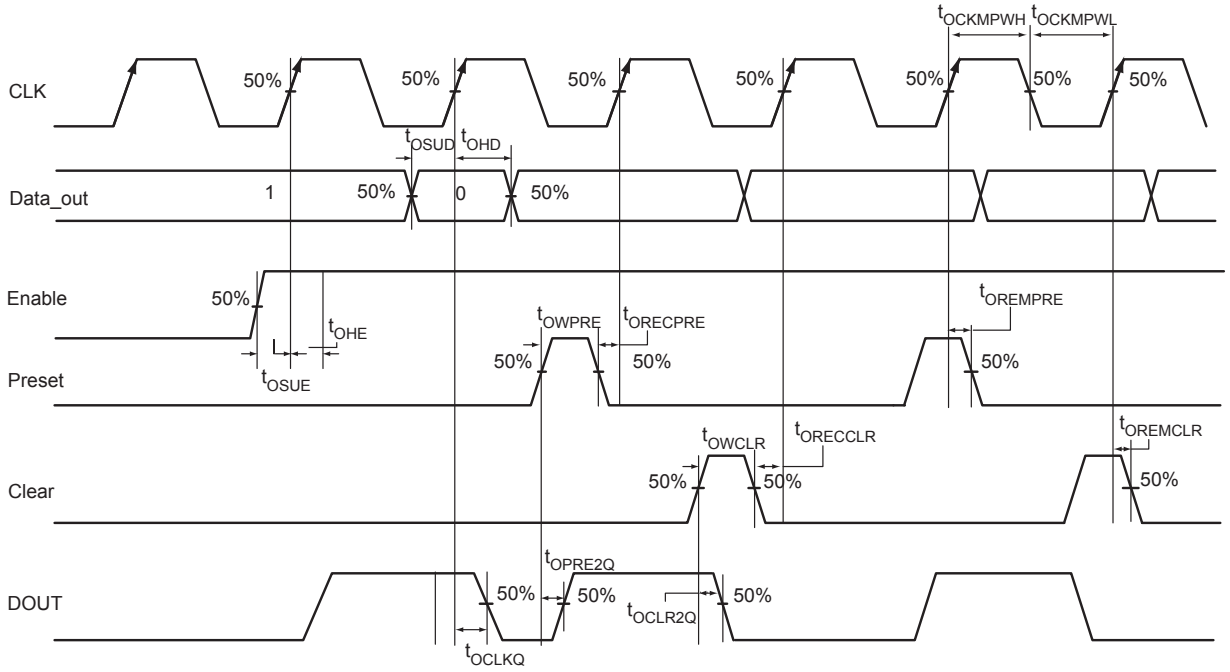

Figure 2-28 • **Output Register Timing Diagram**

Timing Characteristics

Table 2-87 • **Output Data Register Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t_{OCLKQ}	Clock-to-Q of the Output Data Register	0.59	0.67	0.79	ns
t_{OSUD}	Data Setup Time for the Output Data Register	0.31	0.36	0.42	ns
t_{OHD}	Data Hold Time for the Output Data Register	0.00	0.00	0.00	ns
t_{OSUE}	Enable Setup Time for the Output Data Register	0.44	0.50	0.59	ns
t_{OHE}	Enable Hold Time for the Output Data Register	0.00	0.00	0.00	ns
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	0.80	0.91	1.07	ns
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	0.80	0.91	1.07	ns
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	0.00	0.00	0.00	ns
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	0.22	0.25	0.30	ns
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	0.00	0.00	0.00	ns
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	0.22	0.25	0.30	ns
t_{OWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Data Register	0.22	0.25	0.30	ns
t_{OWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Data Register	0.22	0.25	0.30	ns
$t_{OCKMPWH}$	Clock Minimum Pulse Width High for the Output Data Register	0.36	0.41	0.48	ns
$t_{OCKMPWL}$	Clock Minimum Pulse Width Low for the Output Data Register	0.32	0.37	0.43	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

Timing Characteristics

Table 2-95 • A3PE600 Global Resource
Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	–2		–1		Std.		Units
		Min.[1]	Max.[2]	Min.[1]	Max.[2]	Min.[1]	Max.[2]	
t_{RCKL}	Input Low Delay for Global Clock	0.83	1.04	0.94	1.18	1.11	1.39	ns
t_{RCKH}	Input High Delay for Global Clock	0.81	1.06	0.93	1.21	1.09	1.42	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.25		0.28		0.33	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.*

Table 2-96 • A3PE1500 Global Resource
Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	–2		–1		Std.		Units
		Min.[1]	Max.[2]	Min.[1]	Max.[2]	Min.[1]	Max.[2]	
t_{RCKL}	Input Low Delay for Global Clock	1.07	1.29	1.22	1.47	1.43	1.72	ns
t_{RCKH}	Input High Delay for Global Clock	1.06	1.32	1.21	1.50	1.42	1.76	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.26		0.29		0.34	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.*

Table 2-97 • A3PE3000 Global Resource
Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	–2		–1		Std.		Units
		Min.[1]	Max.[2]	Min.[1]	Max.[2]	Min.[1]	Max.[2]	
t_{RCKL}	Input Low Delay for Global Clock	1.41	1.62	1.60	1.85	1.88	2.17	ns
t_{RCKH}	Input High Delay for Global Clock	1.40	1.66	1.59	1.89	1.87	2.22	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.26		0.29		0.35	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.*

Embedded SRAM and FIFO Characteristics

SRAM

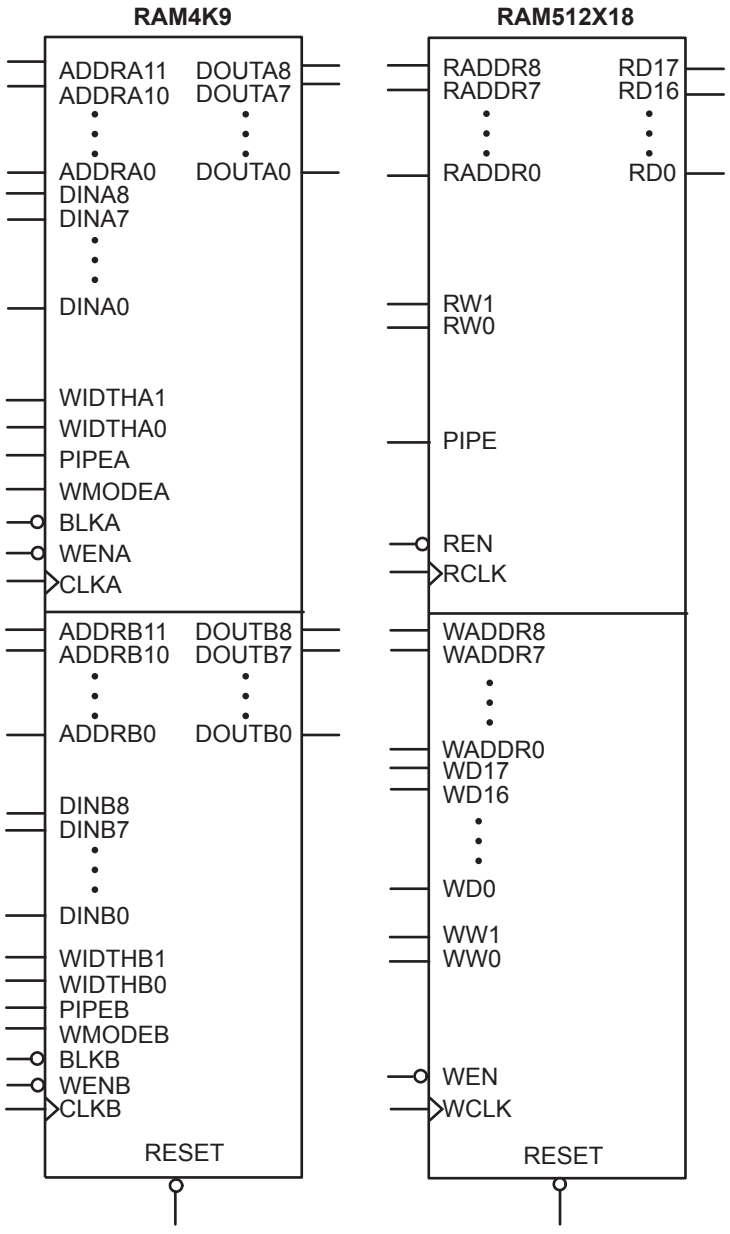

Figure 2-40 • **RAM Models**

Table 2-100 • RAM512X18
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t_{AS}	Address setup time	0.25	0.28	0.33	ns
t_{AH}	Address hold time	0.00	0.00	0.00	ns
t_{ENS}	REN, WEN setup time	0.18	0.20	0.24	ns
t_{ENH}	REN, WEN hold time	0.06	0.07	0.08	ns
t_{DS}	Input data (WD) setup time	0.18	0.21	0.25	ns
t_{DH}	Input data (WD) hold time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to new data valid on RD (output retained)	2.16	2.46	2.89	ns
t_{CKQ2}	Clock High to new data valid on RD (pipelined)	0.90	1.02	1.20	ns
t_{C2CRWH} [1]	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.50	0.43	0.38	ns
t_{C2CWRH} [1]	Address collision clk-to-clk delay for reliable write access after read on same address— Applicable to Opening Edge	0.59	0.50	0.44	ns
t_{RSTBQ}	RESET Low to data out Low on RD (flow-through)	0.92	1.05	1.23	ns
	RESET Low to data out Low on RD (pipelined)	0.92	1.05	1.23	ns
$t_{REMRSTB}$	RESET removal	0.29	0.33	0.38	ns
$t_{RECRSTB}$	RESET recovery	1.50	1.71	2.01	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.21	0.24	0.29	ns
t_{CYC}	Clock cycle time	3.23	3.68	4.32	ns
F_{MAX}	Maximum frequency	310	272	231	MHz

Notes:

1. *For more information, refer to the application note Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.*

3 – Pin Descriptions and Packaging

Supply Pins

GND **Ground**

Ground supply voltage to the core, I/O outputs, and I/O logic.

GNDQ **Ground (quiet)**

Quiet ground supply voltage to input buffers of I/O banks. Within the package, the GNDQ plane is decoupled from the simultaneous switching noise originated from the output buffer ground domain. This minimizes the noise transfer within the package and improves input signal integrity. GNDQ must always be connected to GND on the board.

VCC **Core Supply Voltage**

Supply voltage to the FPGA core, nominally 1.5 V. VCC is required for powering the JTAG state machine in addition to VJTAG. Even when a device is in bypass mode in a JTAG chain of interconnected devices, both VCC and VJTAG must remain powered to allow JTAG signals to pass through the device.

VCCIBx **I/O Supply Voltage**

Supply voltage to the bank's I/O output buffers and I/O logic. Bx is the I/O bank number. There are up to eight I/O banks on low power flash devices plus a dedicated VJTAG bank. Each bank can have a separate VCCI connection. All I/Os in a bank will run off the same VCCIBx supply. VCCI can be 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. In general, unused I/O banks should have their corresponding VCCIX pins tied to GND. If an output pad is terminated to ground through any resistor and if the corresponding VCCIX is left floating, then the leakage current to ground is ~ 0uA. However, if an output pad is terminated to ground through any resistor and the corresponding VCCIX grounded, then the leakage current to ground is ~ 3 uA. For unused banks the aforementioned behavior is to be taken into account while deciding if it’s better to float VCCIX of unused bank or tie it to GND.

VMVx **I/O Supply Voltage (quiet)**

Quiet supply voltage to the input buffers of each I/O bank. *x* is the bank number. Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks. This minimizes the noise transfer within the package and improves input signal integrity. Each bank must have at least one VMV connection, and no VMV should be left unconnected. All I/Os in a bank run off the same VMVx supply. VMV is used to provide a quiet supply voltage to the input buffers of each I/O bank. VMVx can be 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. Unused I/O banks should have their corresponding VMV pins tied to GND. VMV and VCCI should be at the same voltage within a given I/O bank. Used VMV pins must be connected to the corresponding VCCI pins of the same bank (i.e., VMV0 to VCCIB0, VMV1 to VCCIB1, etc.).

VCCPLA/B/C/D/E/F **PLL Supply Voltage**

Supply voltage to analog PLL, nominally 1.5 V.

When the PLLs are not used, the place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground. Microsemi recommends tying VCCPLx to VCC and using proper filtering circuits to decouple VCC noise from the PLLs. Refer to the PLL Power Supply Decoupling section of the "Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" chapter of the *ProASIC3E FPGA Fabric User’s Guide* for a complete board solution for the PLL analog power supply and ground.

There are six VCCPLX pins on ProASIC3E devices.

VCOMPLA/B/C/D/E/F **PLL Ground**

Ground to analog PLL power supplies. When the PLLs are not used, the place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground.

There are six VCOMPL pins (PLL ground) on ProASIC3E devices.

FG484	
Pin Number	**A3PE600 Function**
V15	IO69NDB4V0
V16	GDB2/IO69PDB4V0
V17	TDI
V18	GNDQ
V19	TDO
V20	GND
V21	NC
V22	IO63NDB3V1
W1	NC
W2	NC
W3	NC
W4	GND
W5	IO100NDB5V2
W6	GEB2/IO100PDB5V2
W7	IO99NDB5V2
W8	IO88NDB5V0
W9	IO88PDB5V0
W10	IO89NDB5V0
W11	IO80NDB4V1
W12	IO81NDB4V1
W13	IO81PDB4V1
W14	IO70NDB4V0
W15	GDC2/IO70PDB4V0
W16	IO68NDB4V0
W17	GDA2/IO68PDB4V0
W18	TMS
W19	GND
W20	NC
W21	NC
W22	NC
Y1	VCCIB6
Y2	NC
Y3	NC
Y4	IO98NDB5V2
Y5	GND
Y6	IO94NDB5V1

FG484	
Pin Number	**A3PE600 Function**
Y7	IO94PDB5V1
Y8	VCC
Y9	VCC
Y10	IO89PDB5V0
Y11	IO80PDB4V1
Y12	IO78NPB4V1
Y13	NC
Y14	VCC
Y15	VCC
Y16	NC
Y17	NC
Y18	GND
Y19	NC
Y20	NC
Y21	NC
Y22	VCCIB3

FG484	
Pin Number	**A3PE1500 Function**
V15	IO112NDB4V0
V16	GDB2/IO112PDB4V0
V17	TDI
V18	GNDQ
V19	TDO
V20	GND
V21	NC
V22	IO105NDB3V2
W1	NC
W2	NC
W3	NC
W4	GND
W5	IO165NDB5V3
W6	GEB2/IO165PDB5V3
W7	IO164NDB5V3
W8	IO153NDB5V2
W9	IO153PDB5V2
W10	IO147NDB5V1
W11	IO133NDB4V2
W12	IO130NDB4V2
W13	IO130PDB4V2
W14	IO113NDB4V0
W15	GDC2/IO113PDB4V0
W16	IO111NDB4V0
W17	GDA2/IO111PDB4V0
W18	TMS
W19	GND
W20	NC
W21	NC
W22	NC
Y1	VCCIB6
Y2	NC
Y3	NC
Y4	IO161NDB5V3
Y5	GND
Y6	IO163NDB5V3

FG484	
Pin Number	**A3PE1500 Function**
Y7	IO163PDB5V3
Y8	VCC
Y9	VCC
Y10	IO147PDB5V1
Y11	IO133PDB4V2
Y12	IO131NPB4V2
Y13	NC
Y14	VCC
Y15	VCC
Y16	NC
Y17	NC
Y18	GND
Y19	NC
Y20	NC
Y21	NC
Y22	VCCIB3

FG484	
Pin Number	**A3PE3000 Function**
V15	IO155NDB4V0
V16	GDB2/IO155PDB4V0
V17	TDI
V18	GNDQ
V19	TDO
V20	GND
V21	IO146PDB3V4
V22	IO142NDB3V3
W1	IO239NDB6V0
W2	IO237PDB6V0
W3	IO230PSB5V4
W4	GND
W5	IO232NDB5V4
W6	GEB2/IO232PDB5V4
W7	IO231NDB5V4
W8	IO214NDB5V2
W9	IO214PDB5V2
W10	IO200NDB5V0
W11	IO192NDB4V4
W12	IO184NDB4V3
W13	IO184PDB4V3
W14	IO156NDB4V0
W15	GDC2/IO156PDB4V0
W16	IO154NDB4V0
W17	GDA2/IO154PDB4V0
W18	TMS
W19	GND
W20	IO150NDB3V4
W21	IO146NDB3V4
W22	IO148PPB3V4
Y1	VCCIB6
Y2	IO237NDB6V0
Y3	IO228NDB5V4
Y4	IO224NDB5V3
Y5	GND
Y6	IO220NDB5V3

FG484	
Pin Number	**A3PE3000 Function**
Y7	IO220PDB5V3
Y8	VCC
Y9	VCC
Y10	IO200PDB5V0
Y11	IO192PDB4V4
Y12	IO188NPB4V4
Y13	IO187PSB4V4
Y14	VCC
Y15	VCC
Y16	IO164NDB4V1
Y17	IO164PDB4V1
Y18	GND
Y19	IO158PPB4V0
Y20	IO150PDB3V4
Y21	IO148NPB3V4
Y22	VCCIB3

5 – Datasheet Information

List of Changes

The following table lists critical changes that were made in each revision of the ProASIC3E datasheet.

Revision	Changes	Page
Revision 15 (June 2015)	Updated "ProASIC3E Ordering Information". Interchanged the positions of Y- Security Feature and I- Application (Temperature Range) (SAR 67296). Added Note "Only devices with package size greater than or equal to 5x5 are supported". Updated Commercial and Industrial Junction Temperatures (SAR 67588).	*1-III*
	Added the A3PE3000 package to Table 2-5 (SARs 52320 and 58737).	*2-5*
	Updated "VCCIBx I/O Supply Voltage" (SAR 43323).	*3-1*
Revision 14 (May 2014)	Added 2 mA and 6 mA I/O short currents values in *"I/O Short Currents IOSH/IOSL"* (SAR 56295). Added 2 mA and 6 mA minimum and maximum DC input and output levels in "Minimum and Maximum DC Input and Output Levels"(SAR 56295). Added 3.3 V LVTTL / 3.3 V LVCMOS High Slew Commercial-Case Conditions for 2 mA and 6 mA in "3.3 V LVTTL / 3.3 V LVCMOS High Slew" (SAR 56295). Added 3.3 V LVTTL / 3.3 V LVCMOS Low Slew Commercial-Case Conditions for 2 mA and 6 mA in "3.3 V LVTTL / 3.3 V LVCMOS Low Slew" (SAR 56295).	*2-22* *2-24* *2-25* *2-25*
Revision 13 (January 2013)	In the "Features and Benefits" section, updated the Clock Conditioning Circuit (CCC) and PLL Wide Input Frequency Range from '1.5 MHz to 200 MHz' to '1.5MHz to 350 MHz' based on Table 2-98 (SAR 22196).	1-I
	The "ProASIC3E Ordering Information" section has been updated to mention "Y" as "Blank" mentioning "Device Does Not Include License to Implement IP Based on the Cryptography Research, Inc. (CRI) Patent Portfolio" (SAR 43220).	1-III
	Added a note to "Recommended Operating Conditions [1]" table (SAR 42716): The programming temperature range supported is $T_{ambient}$ = 0°C to 85°C.	2-2
	The note in "ProASIC3E CCC/PLL Specification" table referring the reader to SmartGen was revised to refer instead to the online help associated with the core (SAR 42571).	2-70
	Libero Integrated Design Environment (IDE) was changed to Libero System-on-Chip (SoC) throughout the document (SAR 40285). Live at Power-Up (LAPU) has been replaced with 'Instant On'.	NA
Revision 12 (September 2012)	The "Security" section was modified to clarify that Microsemi does not support read-back of programmed data.	1-1

Revision	Changes	Page
Revision 10 (continued)	"TBD" for 3.3 V LVCMOS Wide Range in Table 2-19 • I/O Output Buffer Maximum Resistances[1] and Table 2-21 • I/O Short Currents IOSH/IOSL was replaced by "Same as regular 3.3 V LVCMOS" (SAR 33853). 3.3 V LVCMOS Wide Range information was separated from regular 3.3 V LVCMOS and placed into its own new section, "3.3 V LVCMOS Wide Range". Values of IOSH and IOSL were added in Table 2-29 • Minimum and Maximum DC Input and Output Levels (SAR 33853).	2-20, 2-27
	The formulas in the table notes for Table 2-20 • I/O Weak Pull-Up/Pull-Down Resistances were corrected (SAR 34755).	2-21
	The AC Loading figures in the "Single-Ended I/O Characteristics" section were updated to match tables in the "Summary of I/O Timing Characteristics – Default I/O Software Settings" section (SAR 34889).	2-24
	The titles and subtitles for Table 2-31 • 3.3 V LVCMOS Wide Range High Slew and Table 2-32 • 3.3 V LVCMOS Wide Range Low Slew were corrected (SAR 37227).	2-28, 2-29
	The following notes were removed from Table 2-78 • LVDS Minimum and Maximum DC Input and Output Levels (SAR 34812): ±5% Differential input voltage = ±350 mV	2-50
	Minimum pulse width High and Low values were added to the tables in the "Global Tree Timing Characteristics" section. The maximum frequency for global clock parameter was removed from these tables because a frequency on the global is only an indication of what the global network can do. There are other limiters such as the SRAM, I/Os, and PLL. SmartTime software should be used to determine the design frequency (SAR 36957).	2-68
	A note was added to Table 2-98 • ProASIC3E CCC/PLL Specification indicating that when the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available (SAR 34824).	2-70
	The following figures were deleted. Reference was made to a new application note, *Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs*, which covers these cases in detail (SAR 34872). Figure 2-44 • Write Access after Write onto Same Address Figure 2-45 • Read Access after Write onto Same Address Figure 2-46 • Write Access after Read onto Same Address The port names in the SRAM "Timing Waveforms", SRAM "Timing Characteristics" tables, Figure 2-49 • FIFO Reset, and the FIFO "Timing Characteristics" tables were revised to ensure consistency with the software names (SAR 35750).	2-74, 2-75, 2-79, 2-82
	The "Pin Descriptions and Packaging" chapter is new (SAR 34771).	3-1
	Package names used in the "Package Pin Assignments" section were revised to match standards given in *Package Mechanical Drawings* (SAR 34771).	4-1
	Pin E6 for the FG256 package was corrected from VvB0 to VCCIB0 (SARs 30364, 31597, 26243).	4-9
July 2010	The versioning system for datasheets has been changed. Datasheets are assigned a revision number that increments each time the datasheet is revised. The "ProASIC3E Device Status" table on page II indicates the status for each device in the device family.	N/A

Revision	Changes	Page
Revision 3 (Apr 2008) Packaging v1.2	The following pins had duplicates and the extra pins were deleted from the "PQ208" A3PE3000 table: 36, 62, 171 Note: There were no pin function changes in this update.	4-2
	The following pins had duplicates and the extra pins were deleted from the "FG324" table: E2, E3, E16, E17, P2, P3, T16, U17 Note: There were no pin function changes in this update.	4-12
	The "FG256" pin table was updated for the A3PE600 device because the old PAT were based on the IFX die, and this is the final UMC die version.	4-9
	The "FG484" was updated for the A3PE600 device because the old PAT were based on the IFX die, and this is the final UMC die version.	4-22
	The following pins had duplicates and the extra pins were deleted from the "FG896" table: AD6, AE5, AE28, AF29, F5, F26, G6, G25 Note: There were no pin function changes in this update.	4-41
Revision 2 (Mar 2008) Product Brief rev. 1	The FG324 package was added to the "ProASIC3E Product Family" table, the "I/Os Per Package1" table, and the "Temperature Grade Offerings" table for A3PE3000.	I, II, IV
Revision 1 (Feb 2008) DC and Switching Characteristics v1.1	In Table 2-3 • Flash Programming Limits – Retention, Storage and Operating Temperature 1, Maximum Operating Junction Temperature was changed from 110°C to 100°C for both commercial and industrial grades.	2
	The "PLL Behavior at Brownout Condition" section is new.	2-4
	In the "PLL Contribution—PPLL" section, the following was deleted: FCLKIN is the input clock frequency.	2-10
	In Table 2-14 • Summary of Maximum and Minimum DC Input Levels, the note was incorrect. It previously said T_J and it was corrected and changed to T_A.	2-17
	In Table 2-98 • ProASIC3E CCC/PLL Specification, the SCLK parameter and note 1 are new.	2-70
	Table 2-103 • JTAG 1532 was populated with the parameter data, which was not in the previous version of the document.	2-83
Revision 1 (cont'd) Packaging v1.1	The "PQ208" pin table for A3PE3000 was updated.	4-2
	The "FG324" pin table for A3PE3000 is new.	4-13
	The "FG484" pin table for A3PE3000 is new.	4-17
	The "FG896" pin table for A3PE3000 is new.	4-41
Revision 0 (Jan 2008)	This document was previously in datasheet v2.1. As a result of moving to the handbook format, Actel has restarted the version numbers. The new version number is 51700098-001-0.	N/A
v2.1 (July 2007)	CoreMP7 information was removed from the "Features and Benefits" section.	1-I
	The M1 device part numbers have been updated in ProASIC3E Product Family, "Packaging Tables", "Temperature Grade Offerings", "Speed Grade and Temperature Grade Matrix", and "Speed Grade and Temperature Grade Matrix".	1-I